11. (Original) The method of claim 9, further comprising:
preheating the underfill material after the carrier substrate is located
adjacent the no-flow underfill material but before the interconnection elements

12. (Original) The method of claim 9, further comprising: holding the microelectronic die with a chuck while the interconnection elements are being reflowed; and releasing the chuck from the microelectronic die.

- 13. (Original) The method of claim 9, wherein the no-flow underfill material is preheated at a temperature between 30°C and 120°C.
- 14. (Original) The method of claim 13, wherein the interconnection elements are reflowed at a temperature of at least 183°C.
- 15. (Currently amended) A method of making a microelectronic assembly, comprising:

assembling a construction including a carrier substrate, a microelectronic die having an integrated circuit, interconnection elements between the carrier substrate and the microelectronic die, and a no-flow underfill material between the interconnection elements;

are reflowed.

no-flew

subsequently heating the underfill material to a temperature below a reflowing temperature of the interconnection elements;

subsequently connecting the <u>microelectronic</u> die with a chuck; and reflowing the interconnection elements by heating the interconnection elements while the <u>microelectronic</u> die is held with the chuck.

- 16. (Original) The method of claim 15, wherein the construction is assembled by dispensing the no-flow underfill material on the carrier substrate.
- 17. (Original) The method of claim 15, wherein the no-flow underfill material is preheated at a temperature between 30°C and 120°C.
- 18. (Original) The method of claim 17, wherein the interconnection elements are reflowed at a temperature of at least 183°C.